

In the Claims:

Please cancel claim 26. Please add new claim 30. Please amend claims 10, 12-16, 18-25, and 27-29 as indicated below. Currently pending claims 10-25 and 27-30 for consideration by the Examiner are as follows:

Claims 1-9 (CANCELED)

C:
sub E1
10. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps performed in the indicated sequential order:

providing a metallic plate such that all exterior surfaces the metallic plate are exposed;

forming a mineral layer on the metallic plate; and

forming an adhesion promoter layer on the mineral layer.

11. (PREVIOUSLY AMENDED) The method of claim 10, wherein forming a the mineral layer includes forming the mineral layer having a mineral selected from the group consisting of silicon dioxide, silicon nitride, and silicon carbide.

12. (CURRENTLY AMENDED) The method of claim 10, wherein forming a the mineral layer includes forming the mineral layer having a thickness between about 50 angstroms and about 2000 angstroms.

13. (CURRENTLY AMENDED) The method of claim 10, wherein forming a the mineral layer

includes sputtering the mineral layer on ~~the~~ a clean surface of the metallic plate.

14. (CURRENTLY AMENDED) The method of claim 10, wherein providing a the metallic plate includes providing the metallic plate having a metallic substance selected from the group consisting of stainless steel, aluminum, titanium, copper, copper coated with nickel, and copper coated with chrome.

15. (CURRENTLY AMENDED) The method of claim 10, wherein forming an the adhesion promoter layer includes forming the adhesion promoter layer having an adhesion promoter selected from the group consisting of a titanate, a zirconate, and an aluminate.

16. (CURRENTLY AMENDED) The method of claim 10, wherein forming an the adhesion promoter layer includes forming the adhesion promoter layer having a silane from the group consisting of 3-glycidoxypropyltrimethoxysilane, 3-glycidoxypropyltriethoxysilane, 3-(2-aminoethyl)propyltrimethoxysilane, and 3-(2-aminoethyl)propyltriethoxysilane.

17. (ORIGINAL) The method of claim 10, further comprising:

providing an electronic assembly;

providing an adhesive material;

coupling the metallic plate to the electronic assembly by interfacing the adhesive material between the adhesion promoter layer and the electronic assembly;

providing an electronic carrier;

coupling the electronic assembly to the electronic carrier; and
coupling the metallic plate to the electronic carrier by interfacing the adhesive material
between the adhesion promoter layer and the electronic carrier.

18. (CURRENTLY AMENDED) The method of claim 17, wherein providing ~~an~~ the adhesive
material includes providing the adhesive material having a structural epoxy adhesive.

19. (CURRENTLY AMENDED) The method of claim 17, wherein providing ~~a~~ the metallic plate
includes providing the metallic plate having a coefficient of thermal expansion (CTE) that
exceeds a CTE of the electronic assembly.

20. (CURRENTLY AMENDED) The ~~structure~~ method of claim 10, further comprising bonding
the adhesion promoter layer to a structural adhesive.

21. (CURRENTLY AMENDED) The ~~structure~~ method of claim 10, wherein the adhesion
promoter layer has a thickness between 1 monolayer and about 50 monolayers.

22. (CURRENTLY AMENDED) The method of claim 10, wherein forming ~~an~~ the adhesion
promoter layer includes forming the adhesion promoter layer comprising a chemical compound
in crystalline form.

23. (CURRENTLY AMENDED) The method of claim 10, wherein forming ~~an~~ the adhesion

promoter layer includes forming the adhesion promoter layer comprising a chemical compound in amorphous form.

24. (CURRENTLY AMENDED) The method of claim 10, wherein forming ~~a~~ the mineral layer comprises forming the mineral layer covering an edge surface of the metallic plate and a portion of a top surface of the metallic plate.

25. (CURRENTLY AMENDED) The method of claim 10, wherein forming ~~a~~ the mineral layer includes forming the mineral layer having a thickness between about 100 angstroms and about 1000 angstroms.

27. (CURRENTLY AMENDED) The method of claim 10, wherein forming ~~an~~ the adhesion promoter layer includes forming the adhesion promoter layer having an adhesion promoter comprising a silane.

28. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps performed in the indicated sequential order:

providing a metallic plate such that all exterior surfaces the metallic plate are exposed;

bonding a mineral layer to a the metallic plate; and

covalently bonding an adhesion promoter layer to the mineral layer.

29. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps performed in the indicated sequential order:

providing a metallic plate such that all exterior surfaces the metallic plate are exposed;

bonding a mineral layer to a the metallic plate; and

bonding an adhesion promoter layer to the mineral layer such that said bonding to the mineral layer is moisture resistant.

30. (NEW) The method of claim 10, wherein providing the metallic plate includes providing the metallic plate having a metallic substance selected from the group consisting of stainless steel, titanium, copper, copper coated with nickel, and copper coated with chrome.